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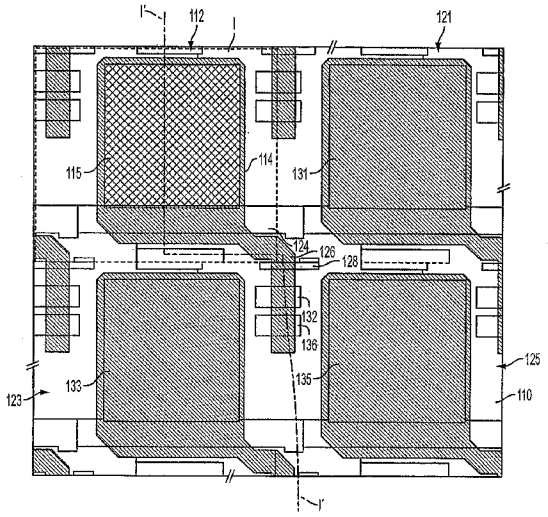
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(54) **Title:** REDUCED IMAGER CROSSTALK AND PIXEL NOISE USING EXTENDED BURIED CONTACTS



(57) **Abstract:** Methods and structures to reduce the occurrence of crosstalk and pixel noise in solid state imager arrays. In an exemplary embodiment, a section of a layer patterned to form polysilicon buried-contacts in the pixel structure is also patterned to be disposed over the active, photosensor portion of the pixel. The section of the buried-contact layer covering the photosensor portion of the pixel serves to filter the light striking the buried-contact layer before the light strikes the photosensor. The polysilicon light filter reduces the amount of stray light entering from the adjacent pixels without adding significant processing complexity.

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